Abstract

Epitaxially coated silicon wafer with <110> orientation and method for producing it

An epitaxially coated silicon wafer, comprising a plane misoriented relative to a {110} crystal plane as wafer surface, wherein the <110> direction is tilted away by the angle θ from the normal to the wafer surface and the projection of the tilted <110> direction forms an angle φ with the direction <-110> in the wafer plane and θ is given by $0 \leq \theta \leq 3°$ and $45° \leq \varphi \leq 90°$ (and all symmetrically equivalent directions).

Fig. 1